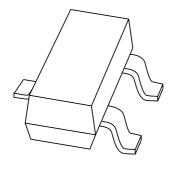
DISCRETE SEMICONDUCTORS

DATA SHEET



BAS19; BAS20; BAS21 General purpose diodes

Product data sheet Supersedes data of 1999 May 26 2003 Mar 20



General purpose diodes

BAS19; BAS20; BAS21

FEATURES

- Small plastic SMD package
- Switching speed: max. 50 ns
- · General application
- Continuous reverse voltage: max. 100 V; 150 V; 200 V
- Repetitive peak reverse voltage: max. 120 V; 200 V; 250 V
- Repetitive peak forward current: max. 625 mA.

APPLICATIONS

General purpose switching in e.g. surface mounted circuits.

DESCRIPTION

The BAS19, BAS20 and BAS21 are general purpose diodes fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

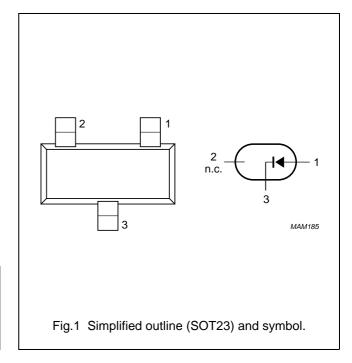
TYPE NUMBER	MARKING CODE (1)
BAS19	JP*
BAS20	JR*
BAS21	JS*

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

PINNING

PIN	DESCRIPTION		
1	anode		
2	not connected		
3	cathode		



General purpose diodes

BAS19; BAS20; BAS21

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage				
	BAS19		_	120	V
	BAS20		_	200	V
	BAS21		_	250	V
V _R	continuous reverse voltage				
	BAS19		_	100	V
	BAS20		_	150	V
	BAS21		_	200	V
I _F	continuous forward current	see Fig.2; note 1	_	200	mA
I _{FRM}	repetitive peak forward current		-	625	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	9	Α
		t = 100 μs	_	3	Α
		t = 10 ms	_	1.7	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

^{1.} Device mounted on an FR4 printed-circuit board.

General purpose diodes

BAS19; BAS20; BAS21

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.3		
		$I_{F} = 100 \text{ mA}$	1	V
		I _F = 200 mA	1.25	V
I _R	reverse current	see Fig.5		
	BAS19	V _R = 100 V	100	nA
		V _R = 100 V; T _j = 150 °C	100	μΑ
	BAS20	V _R = 150 V	100	nA
		V _R = 150 V; T _j = 150 °C	100	μΑ
	BAS21	V _R = 200 V	100	nA
		V _R = 200 V; T _j = 150 °C	100	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	5	pF
t _{rr}	reverse recovery time	when switched from I _F = 30 mA to	50	ns
		I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA; see Fig.8		

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		330	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

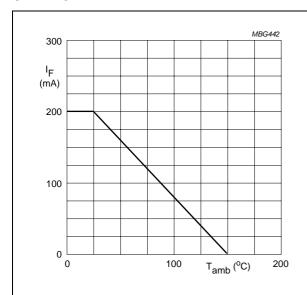
1. Device mounted on an FR4 printed-circuit board.

2003 Mar 20

General purpose diodes

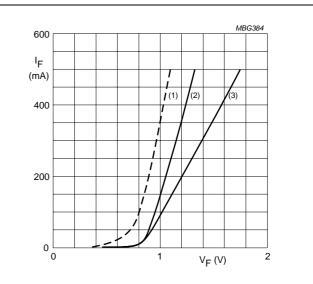
BAS19; BAS20; BAS21

GRAPHICAL DATA



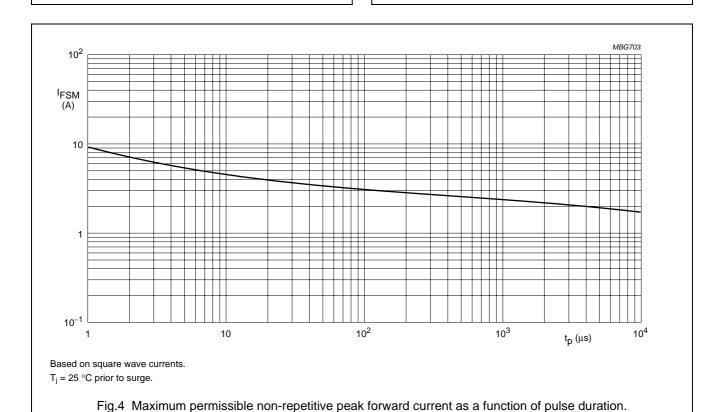
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_i = 150 \,^{\circ}\text{C}$; typical values.
- (2) T_i = 25 °C; typical values.
- (3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

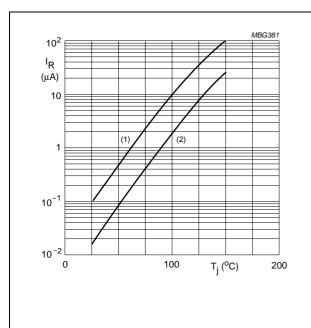


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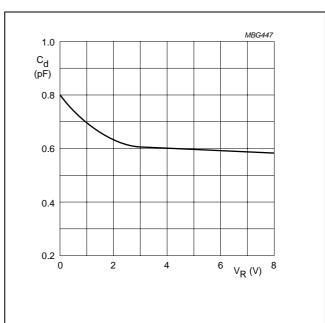
General purpose diodes

BAS19; BAS20; BAS21



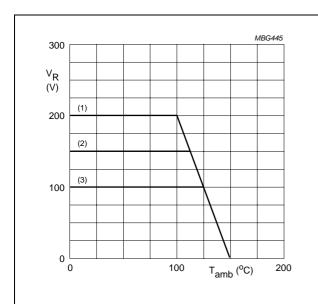
- (1) $V_R = V_{Rmax}$; maximum values.
- (2) $V_R = V_{Rmax}$; typical values.

Fig.5 Reverse current as a function of junction temperature.



 $f = 1 \text{ MHz}; T_j = 25 \,^{\circ}\text{C}.$

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

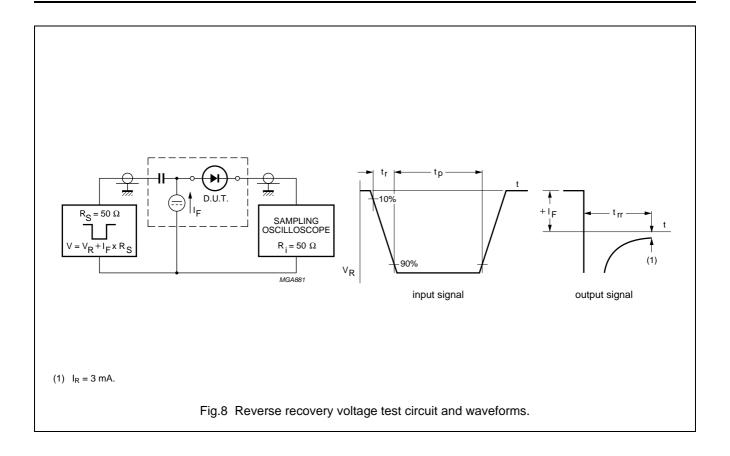


- (1) BAS21.
- (2) BAS20.
- (3) BAS19.

Fig.7 Maximum permissible continuous reverse voltage as a function of the ambient temperature.

General purpose diodes

BAS19; BAS20; BAS21



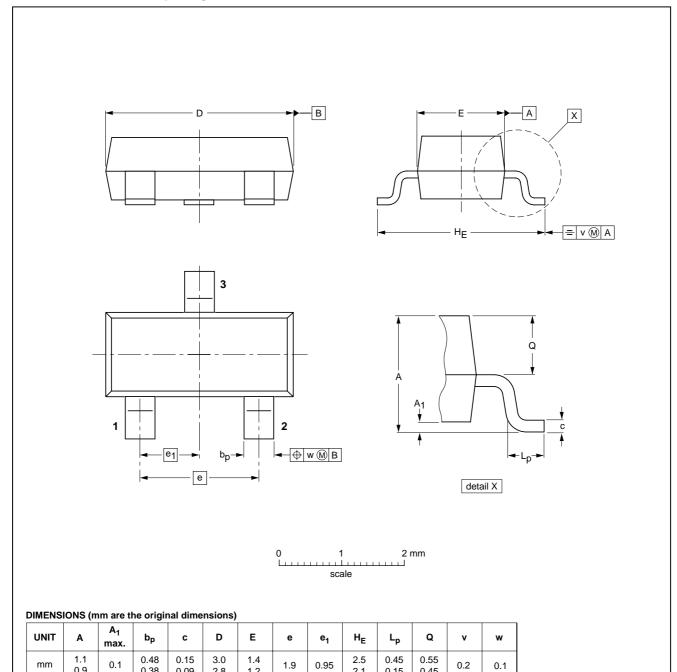
General purpose diodes

BAS19; BAS20; BAS21

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



ou	TLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VEF	RSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
S	OT23		TO-236AB				97-02-28 99-09-13

0.15

0.45

2003 Mar 20 8

0.38

0.09

2.8

General purpose diodes

BAS19; BAS20; BAS21

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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